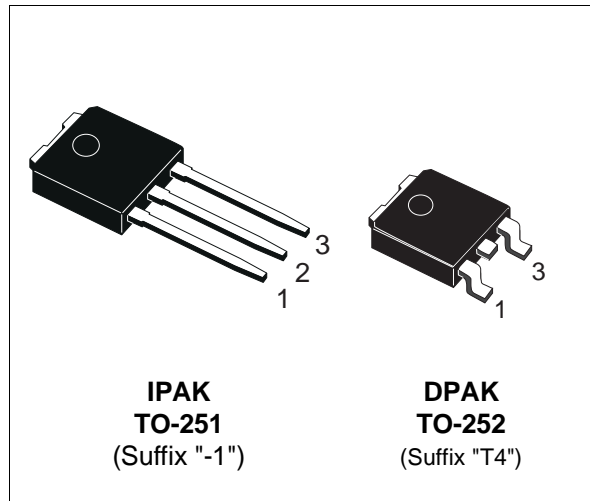


N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

PRELIMINARY DATA

| TYPE | V _{DSS} | R _{DS(on)} | I _D |
|----------|------------------|---------------------|----------------|
| STD2NA50 | 500 V | < 4 Ω | 2.2 A |

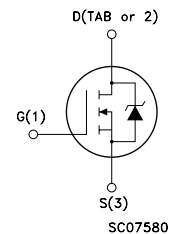
- TYPICAL R_{DS(on)} = 3.25 Ω
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED
- REDUCED THRESHOLD VOLTAGE SPREAD
- THROUGH-HOLE IPAK (TO-251) POWER PACKAGE IN TUBE (SUFFIX "-1")
- SURFACE-MOUNTING DPAK (TO-252) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")



APPLICATIONS

- MEDIUM CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CONSUMER AND INDUSTRIAL LIGHTING

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|---------------------|---|------------|------|
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 500 | V |
| V _{DGR} | Drain- gate Voltage (R _{GS} = 20 kΩ) | 500 | V |
| V _{GS} | Gate-source Voltage | ± 30 | V |
| I _D | Drain Current (continuous) at T _c = 25 °C | 2.2 | A |
| I _D | Drain Current (continuous) at T _c = 100 °C | 1.4 | A |
| I _{DM} (•) | Drain Current (pulsed) | 8.8 | A |
| P _{tot} | Total Dissipation at T _c = 25 °C | 45 | W |
| | Derating Factor | 0.36 | W/°C |
| T _{stg} | Storage Temperature | -65 to 150 | °C |
| T _j | Max. Operating Junction Temperature | 150 | °C |

(•) Pulse width limited by safe operating area

STD2NA50

THERMAL DATA

| | | | | |
|-----------------------|--|-----|------|------|
| R _{thj-case} | Thermal Resistance Junction-case | Max | 2.78 | °C/W |
| R _{thj-amb} | Thermal Resistance Junction-ambient | Max | 100 | °C/W |
| R _{thc-sink} | Thermal Resistance Case-sink | Typ | 1 | °C/W |
| T _l | Maximum Lead Temperature For Soldering Purpose | | 275 | °C |

AVALANCHE CHARACTERISTICS

| Symbol | Parameter | Max Value | Unit |
|-----------------|--|-----------|------|
| I _{AR} | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%) | 2.2 | A |
| E _{AS} | Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V) | 25 | mJ |
| E _{AR} | Repetitive Avalanche Energy (pulse width limited by T _j max, δ < 1%) | 1 | mJ |
| I _{AR} | Avalanche Current, Repetitive or Not-Repetitive (T _c = 100 °C, pulse width limited by T _j max, δ < 1%) | 1.4 | A |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------|---|--|------|------|-------------|----------|
| V _{(BR)DSS} | Drain-source Breakdown Voltage | I _D = 250 μA V _{GS} = 0 | 500 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current (V _{GS} = 0) | V _{DS} = Max Rating V _{DS} = Max Rating x 0.8 T _c = 125 °C | | | 250 1000 | μA μA |
| I _{GSS} | Gate-Source Leakage Current (V _{DS} = 0) | V _{GS} = ± 30 V | | | 100 | mA |

ON (*)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|-----------------------------------|--|------|------|--------|--------|
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} I _D = 250 μA | 2.25 | 3 | 3.75 | V |
| R _{DS(on)} | Static Drain-source On Resistance | V _{GS} = 10 V I _D = 1.1 A V _{GS} = 10 V I _D = 1.1 A T _c = 100 °C | | 3.25 | 4 8 | Ω Ω |
| I _{D(on)} | On State Drain Current | V _{DS} > I _{D(on)} x R _{DS(on)max} V _{GS} = 10 V | 2.2 | | | A |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|--|------|------|------|------|
| g _{fs} (*) | Forward Transconductance | V _{DS} > I _{D(on)} x R _{DS(on)max} I _D = 1.1 A | 0.7 | 1.9 | | S |
| C _{iss} | Input Capacitance | V _{DS} = 25 V f = 1 MHz V _{GS} = 0 | | 300 | 400 | pF |
| C _{oss} | Output Capacitance | | | 55 | 70 | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 15 | 20 | pF |

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------|--|---|------|----------------|----------|------------------|
| $t_{d(on)}$ t_r | Turn-on Time Rise Time | $V_{DD} = 250\text{ V}$ $R_G = 4.7\ \Omega$ | | 7 8 | 10 11 | ns ns |
| $(di/dt)_{on}$ | Turn-on Current Slope | $V_{DD} = 400\text{ V}$ $R_G = 47\ \Omega$ | | 350 | | A/ μs |
| Q_g Q_{gs} Q_{gd} | Total Gate Charge Gate-Source Charge Gate-Drain Charge | $V_{DD} = 400\text{ V}$ $I_D = 2.2\text{ A}$ $V_{GS} = 10\text{ V}$ | | 18 5.5 7 | 25 | nC nC nC |

SWITCHING OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------------------|---|--|------|--------------|----------------|----------------|
| $t_{r(Voff)}$ t_f t_c | Off-voltage Rise Time Fall Time Cross-over Time | $V_{DD} = 400\text{ V}$ $R_G = 4.7\ \Omega$ | | 7 7 14 | 10 10 20 | ns ns ns |

SOURCE DRAIN DIODE

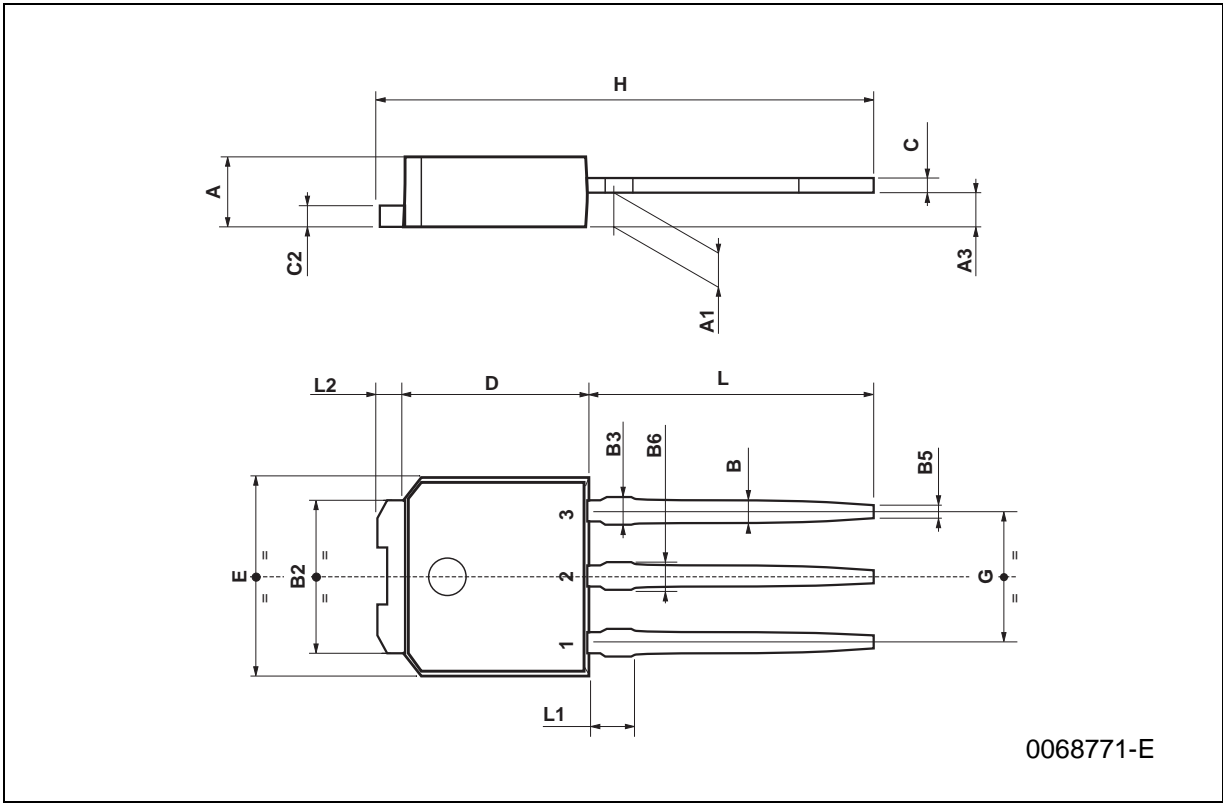
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------------------------|--|---|------|------------------|------------|--------------------------|
| I_{SD} $I_{SDM}(\bullet)$ | Source-drain Current Source-drain Current (pulsed) | | | | 2.2 8.8 | A A |
| $V_{SD} (*)$ | Forward On Voltage | $I_{SD} = 2.2\text{ A}$ $V_{GS} = 0$ | | | 1.6 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current | $I_{SD} = 2.2\text{ A}$ $V_{DD} = 100\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ $T_j = 150\text{ }^\circ\text{C}$ | | 380 4.4 23 | | ns μC A |

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

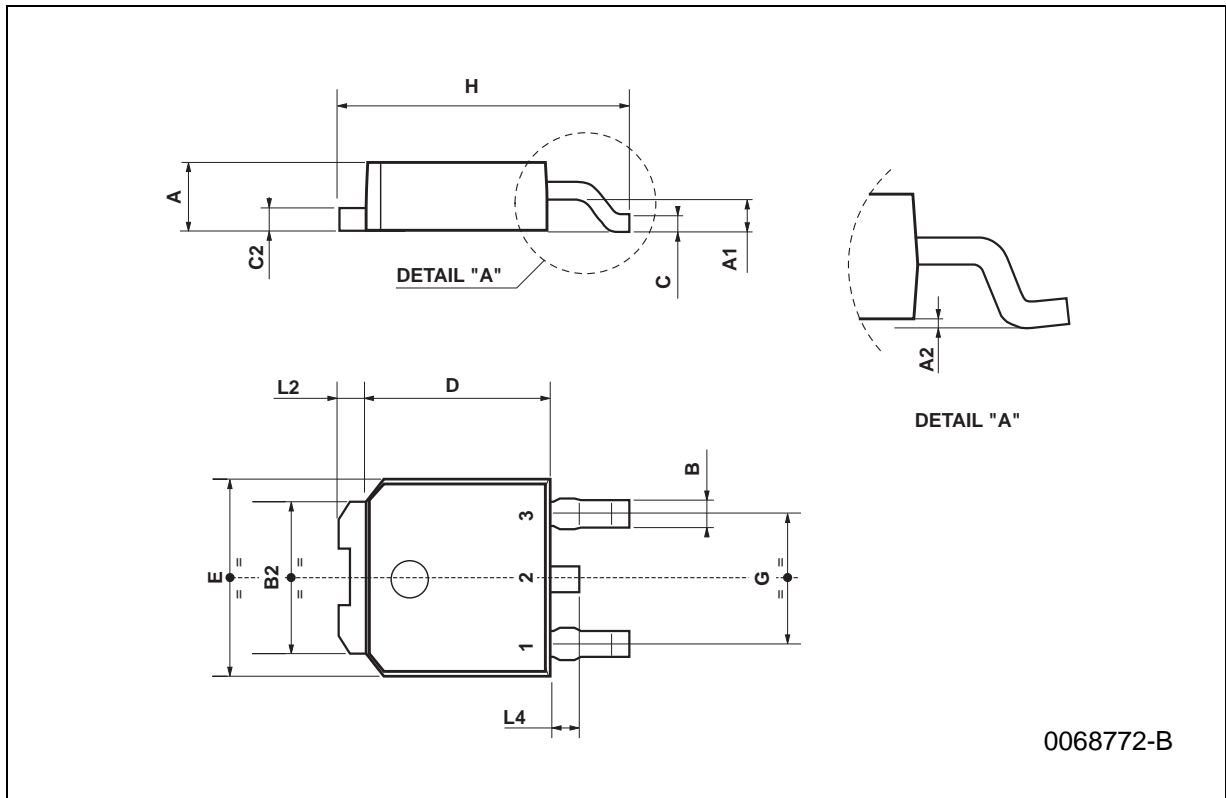
TO-251 (IPAK) MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 2.2 | | 2.4 | 0.086 | | 0.094 |
| A1 | 0.9 | | 1.1 | 0.035 | | 0.043 |
| A3 | 0.7 | | 1.3 | 0.027 | | 0.051 |
| B | 0.64 | | 0.9 | 0.025 | | 0.031 |
| B2 | 5.2 | | 5.4 | 0.204 | | 0.212 |
| B3 | | | 0.85 | | | 0.033 |
| B5 | | 0.3 | | | 0.012 | |
| B6 | | | 0.95 | | | 0.037 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 0.48 | | 0.6 | 0.019 | | 0.023 |
| D | 6 | | 6.2 | 0.236 | | 0.244 |
| E | 6.4 | | 6.6 | 0.252 | | 0.260 |
| G | 4.4 | | 4.6 | 0.173 | | 0.181 |
| H | 15.9 | | 16.3 | 0.626 | | 0.641 |
| L | 9 | | 9.4 | 0.354 | | 0.370 |
| L1 | 0.8 | | 1.2 | 0.031 | | 0.047 |
| L2 | | 0.8 | 1 | | 0.031 | 0.039 |



TO-252 (DPAK) MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 2.2 | | 2.4 | 0.086 | | 0.094 |
| A1 | 0.9 | | 1.1 | 0.035 | | 0.043 |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 |
| B | 0.64 | | 0.9 | 0.025 | | 0.035 |
| B2 | 5.2 | | 5.4 | 0.204 | | 0.212 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 0.48 | | 0.6 | 0.019 | | 0.023 |
| D | 6 | | 6.2 | 0.236 | | 0.244 |
| E | 6.4 | | 6.6 | 0.252 | | 0.260 |
| G | 4.4 | | 4.6 | 0.173 | | 0.181 |
| H | 9.35 | | 10.1 | 0.368 | | 0.397 |
| L2 | | 0.8 | | | 0.031 | |
| L4 | 0.6 | | 1 | 0.023 | | 0.039 |



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